



850 nm Single Mode VCSEL Chip

CG1165 Series

Application: Position Sensing / Pointing device for computer

Absolute Maximum Ratings (T = 25°C)

Parameter	Symbol	Unit	Min.	Max.	Note
Forward current	I _{max}	mA		12	
Reverse voltage	V _r	V	5		I _r = -10uA
Operating temperature	T _{op}	°C	0	45	
Storage temperature	T _{stg}	°C	-40	85	
Maximum die exposure	T _{max}	°C		260	for 10 sec.

Electro-Optical Characteristics (T = 25°C, unless noted otherwise):

Parameter	Symbol	Unit	Min.	Typ	Max.	Test Condition
Threshold Current	I _{th}	mA	1	2	3	—
Operating Voltage	V _{op}	V	—	2.0	2.5	@0.5mW
Differential resistance	R _s	Ω	—	60	130	I _f =5mA
Reverse voltage	V _r	V	5	—	—	I _r =-10uA
Slope efficiency	η	mW/mA	0.1	0.2	0.4	I _f =5mA
Side mode suppression ratio	SMSR	dB	20	30	—	@0.5mW
Peak Wavelength	λ	nm	830	845	860	@0.5mW
Beam Divergence Angle	θ	deg	—	12	—	full width, 1/e ²
Optical output power	P _o	mW	Bin A: 0.25~0.30			@3.5mA
			Bin B: 0.30~0.40			
			Bin C: 0.40~0.50			
			Bin D: 0.50~0.60			
			Bin E: 0.60~0.70			
			Bin F: 0.70~0.90			

■ Outline Configuration (unit: μm)

1. Top contact: Anode; Bottom contact: Cathode.
2. Dimension: 220 μm (width) x 220 μm (length) x 100 μm (thickness)
Tolerance: ±12.5μm
3. Bond pad size: 80μm diameter